Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4287	(438/424,425,431,435,436,437, 695,700,702,759).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:48
L3	576	high adj density adj plasma and temperature same substrate and silicon adj dioxide and etch adj rate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 07:49
L4	56	l1 and L3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/13 07:49
L5	1517	(438/424).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:49
L6	251	(438/425).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:50
L7	171	(438/431).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:50
L8	515	(438/435).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:50
L9	73	(438/436).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:51
L10	343	(438/437).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:50
L11	995	(438/700).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:51
L12	913	(438/702).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/13 07:51

| L13 | 204 | (438/759).CCLS. | US-PGPUB;
USPAT;
USOCR;
EPO; JPO | OR | OFF | 2005/07/13 07:51 |

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	375	high adj density adj plasma and proximate same substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/22 14:31
S2	229	high adj density adj plasma and proximate same substrate and silicon adj dioxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:51
S3	64	high adj density adj plasma and proximate same substrate and silicon adj dioxide and etch adj rate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 12:05
S4	2	(("6737328") or ("6759306")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/06/07 11:55
S5	566	high adj density adj plasma and temperature same substrate and silicon adj dioxide and etch adj rate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 15:16
S6	286	high adj density adj plasma and temperature near substrate and silicon adj dioxide and etch adj rate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 15:16